

74LVC3G17

Triple non-inverting Schmitt trigger with 5 V tolerant input

Rev. 06 — 6 June 2008

Product data sheet

1. General description

The 74LVC3G17 provides three non-inverting buffers with Schmitt trigger action. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC3G17 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low-power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C

3. Applications

- Wave and pulse shapers for highly noisy environments

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC3G17DP	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC3G17DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC3G17GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC3G17GD	-40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
74LVC3G17GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

5. Marking

Table 2. Marking codes

Type number	Marking code
74LVC3G17DP	V17
74LVC3G17DC	V17
74LVC3G17GT	V17
74LVC3G17GD	V17
74LVC3G17GM	V17

6. Functional diagram

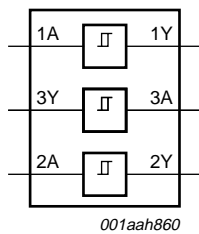


Fig 1. Logic symbol

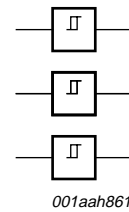


Fig 2. IEC logic symbol

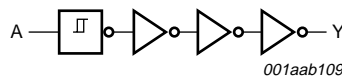
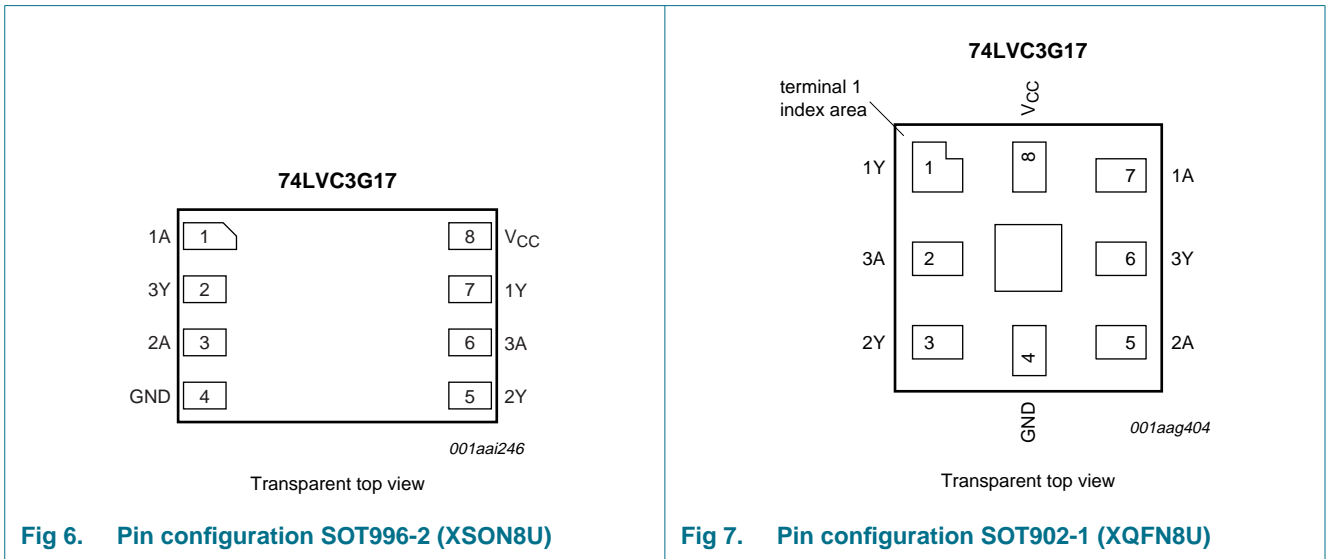
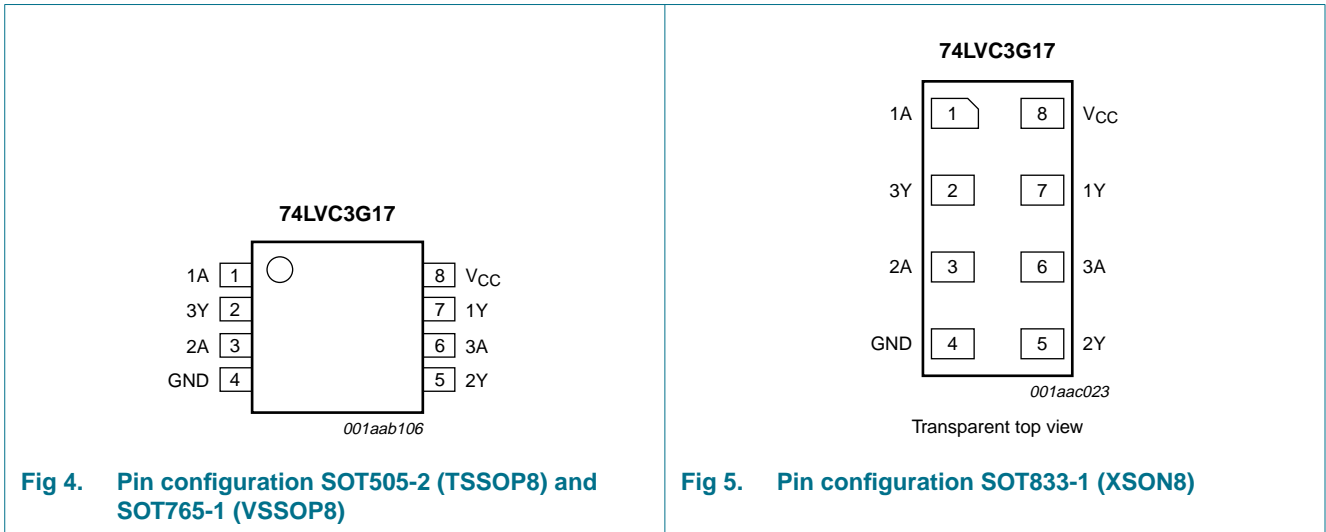


Fig 3. Logic diagram (one gate)

7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output
V _{CC}	8	8	supply voltage

8. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
V _I	input voltage		^[1] -0.5	+6.5	V
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
V _O	output voltage	Active mode	^[1] -0.5	V _{CC} + 0.5	V
		Power-down mode	^{[1][2]} -0.5	+6.5	V
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage		0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$						
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100\ \mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	-	0.1	V
		$I_O = 4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.45	V
		$I_O = 8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.3	V
		$I_O = 12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	-	-	0.4	V
		$I_O = 24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.55	V
		$I_O = 32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	-	0.55	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100\ \mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	$V_{CC} - 0.1$	-	-	V
		$I_O = -4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	1.2	-	-	V
		$I_O = -8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	1.9	-	-	V
		$I_O = -12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	2.2	-	-	V
		$I_O = -24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	2.3	-	-	V
		$I_O = -32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	3.8	-	-	V
I_I	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 0\text{ V to }5.5\text{ V}$	[2] -	± 0.1	± 5	μA
I_{OFF}	power-off leakage current	V_I or $V_O = 5.5\text{ V}$; $V_{CC} = 0\text{ V}$	-	± 0.1	± 10	μA
I_{CC}	supply current	$V_I = 5.5\text{ V}$ or GND; $I_O = 0\text{ A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	0.1	10	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6\text{ V}$; $I_O = 0\text{ A}$; $V_{CC} = 2.3\text{ V to }5.5\text{ V}$	[2] -	5	500	μA
C_I	input capacitance		-	3.5	-	pF
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100\ \mu\text{A}$; $V_{CC} = 1.65\text{ V to }5.5\text{ V}$	-	-	0.1	V
		$I_O = 4\text{ mA}$; $V_{CC} = 1.65\text{ V}$	-	-	0.70	V
		$I_O = 8\text{ mA}$; $V_{CC} = 2.3\text{ V}$	-	-	0.45	V
		$I_O = 12\text{ mA}$; $V_{CC} = 2.7\text{ V}$	-	-	0.60	V
		$I_O = 24\text{ mA}$; $V_{CC} = 3.0\text{ V}$	-	-	0.80	V
		$I_O = 32\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	-	0.80	V

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	0.95	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.7	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	1.9	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.0	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.4	-	-	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±20	μA
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	-	±20	μA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	-	40	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5	mA

- [1] All typical values are measured at T_{amb} = 25 °C.
- [2] These typical values are measured at V_{CC} = 3.3 V.

12. Dynamic characteristics

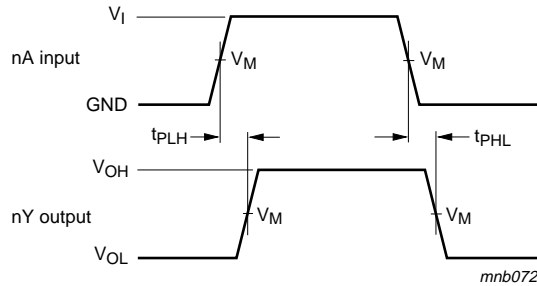
Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 8 ^[2]						
		V _{CC} = 1.65 V to 1.95 V	1.5	5.6	10.5	1.5	13.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	3.7	6.5	1.0	8.5	ns
		V _{CC} = 2.7 V	1.0	3.8	6.5	1.0	8.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	3.6	5.7	1.0	7.1	ns
		V _{CC} = 4.5 V to 5.5 V	1.0	2.7	4.3	1.0	5.4	ns
C _{PD}	power dissipation capacitance	per buffer; V _{CC} = 3.3 V; V _I = GND to V _{CC} ^[3]	-	16.3	-	-	-	pF

- [1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of outputs.

13. Waveforms

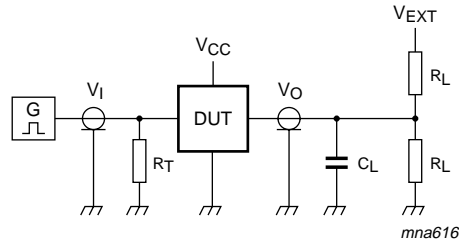


Measurement points are given in [Table 9](#).
 V_{OL} and V_{OH} are typical output voltage drops that occur with the output load.

Fig 8. The input (nA) to output (nY) propagation delays and the output transition times

Table 9. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _M
1.65 V to 1.95 V	0.5 × V _{CC}	0.5 × V _{CC}
2.3 V to 2.7 V	0.5 × V _{CC}	0.5 × V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × V _{CC}	0.5 × V _{CC}



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 9. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

14. Transfer characteristics

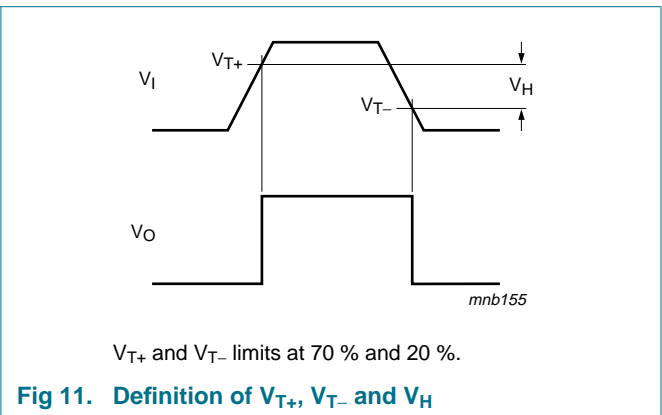
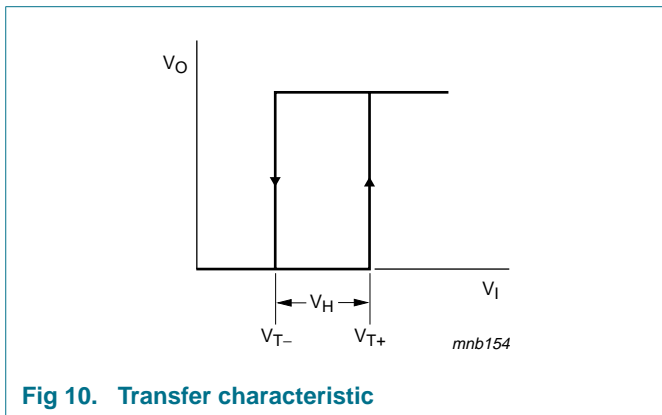
Table 11. Transfer characteristics

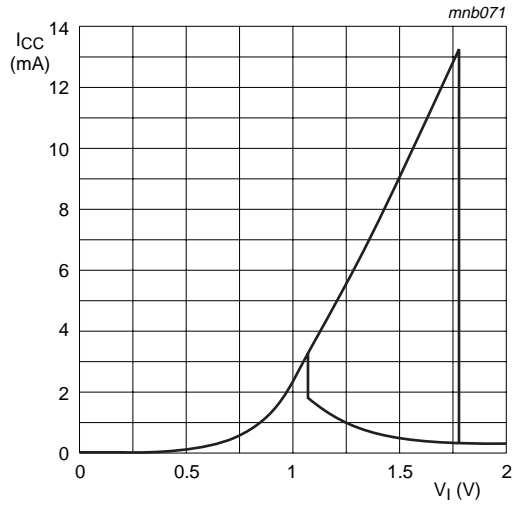
At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{T+}	positive-going threshold voltage	see Figure 10 and Figure 11						
		V _{CC} = 1.8 V	0.70	1.10	1.50	0.70	1.70	V
		V _{CC} = 2.3 V	1.00	1.40	1.80	1.00	2.00	V
		V _{CC} = 3.0 V	1.30	1.76	2.20	1.30	2.40	V
		V _{CC} = 4.5 V	1.90	2.47	3.10	1.90	3.30	V
V _{T-}	negative-going threshold voltage	see Figure 10 and Figure 11						
		V _{CC} = 1.8 V	0.25	0.61	0.90	0.25	1.10	V
		V _{CC} = 2.3 V	0.40	0.80	1.15	0.40	1.35	V
		V _{CC} = 3.0 V	0.60	1.04	1.50	0.60	1.70	V
		V _{CC} = 4.5 V	1.00	1.55	2.00	1.00	2.20	V
V _H	hysteresis voltage (V _{T+} - V _{T-}); see Figure 10 , Figure 11 and Figure 12	V _{CC} = 1.8 V	0.15	0.49	1.00	0.15	1.20	V
		V _{CC} = 2.3 V	0.25	0.60	1.10	0.25	1.30	V
		V _{CC} = 3.0 V	0.40	0.73	1.20	0.40	1.40	V
		V _{CC} = 4.5 V	0.60	0.92	1.50	0.60	1.70	V
		V _{CC} = 5.5 V	0.70	1.02	1.70	0.70	1.90	V

[1] All typical values are measured at T_{amb} = 25 °C.

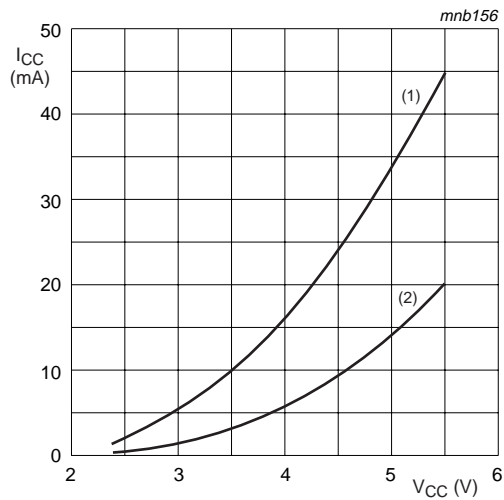
15. Waveforms transfer characteristics





$V_{CC} = 3.0$ V.

Fig 12. Typical transfer characteristic



- (1) Positive-going edge.
- (2) Negative-going edge.

Linear change of V_1 between 0.8 V to 2.0 V. All values given are typical unless otherwise specified.

Fig 13. Average I_{CC} as a function of V_{CC}

16. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

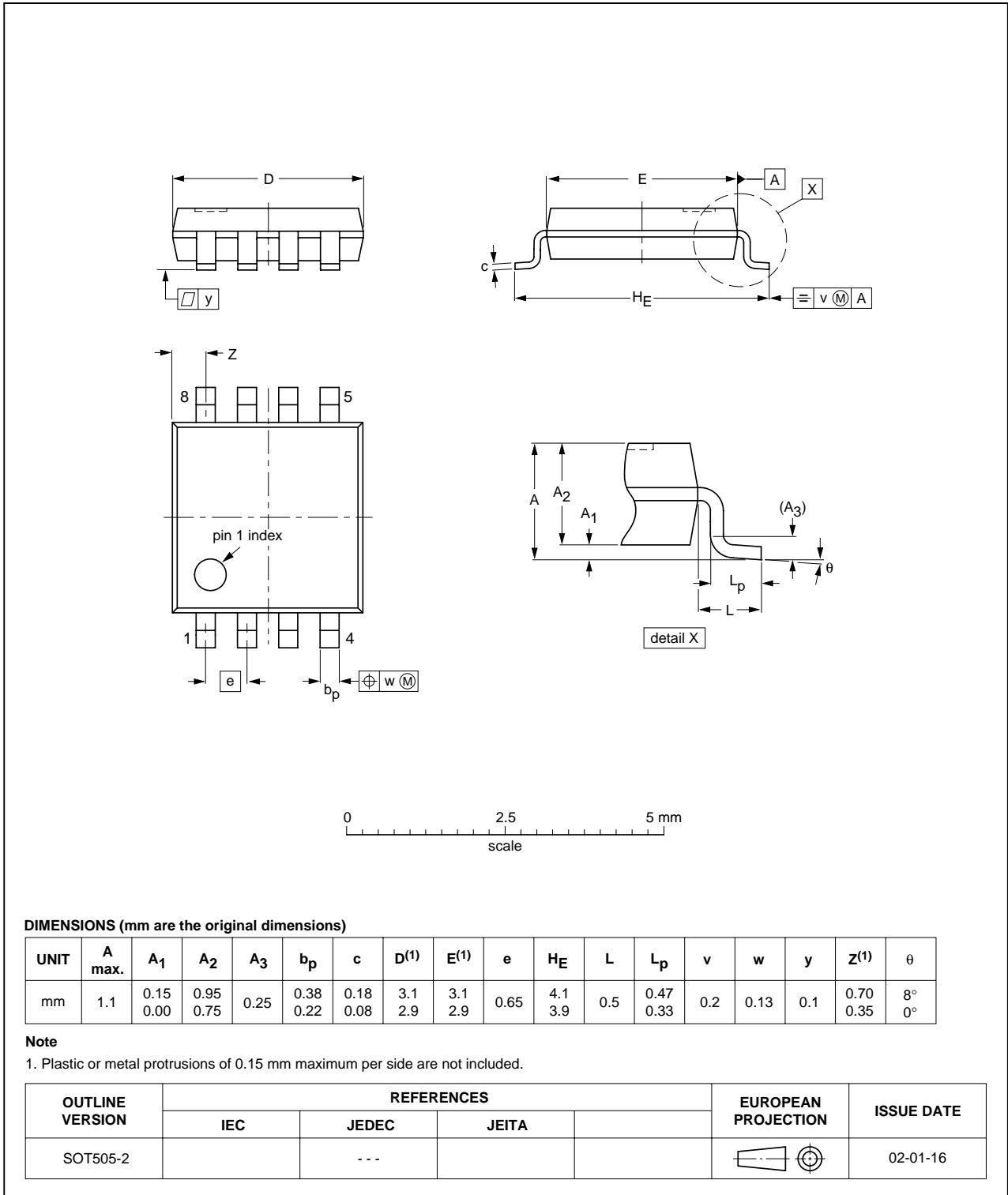


Fig 14. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

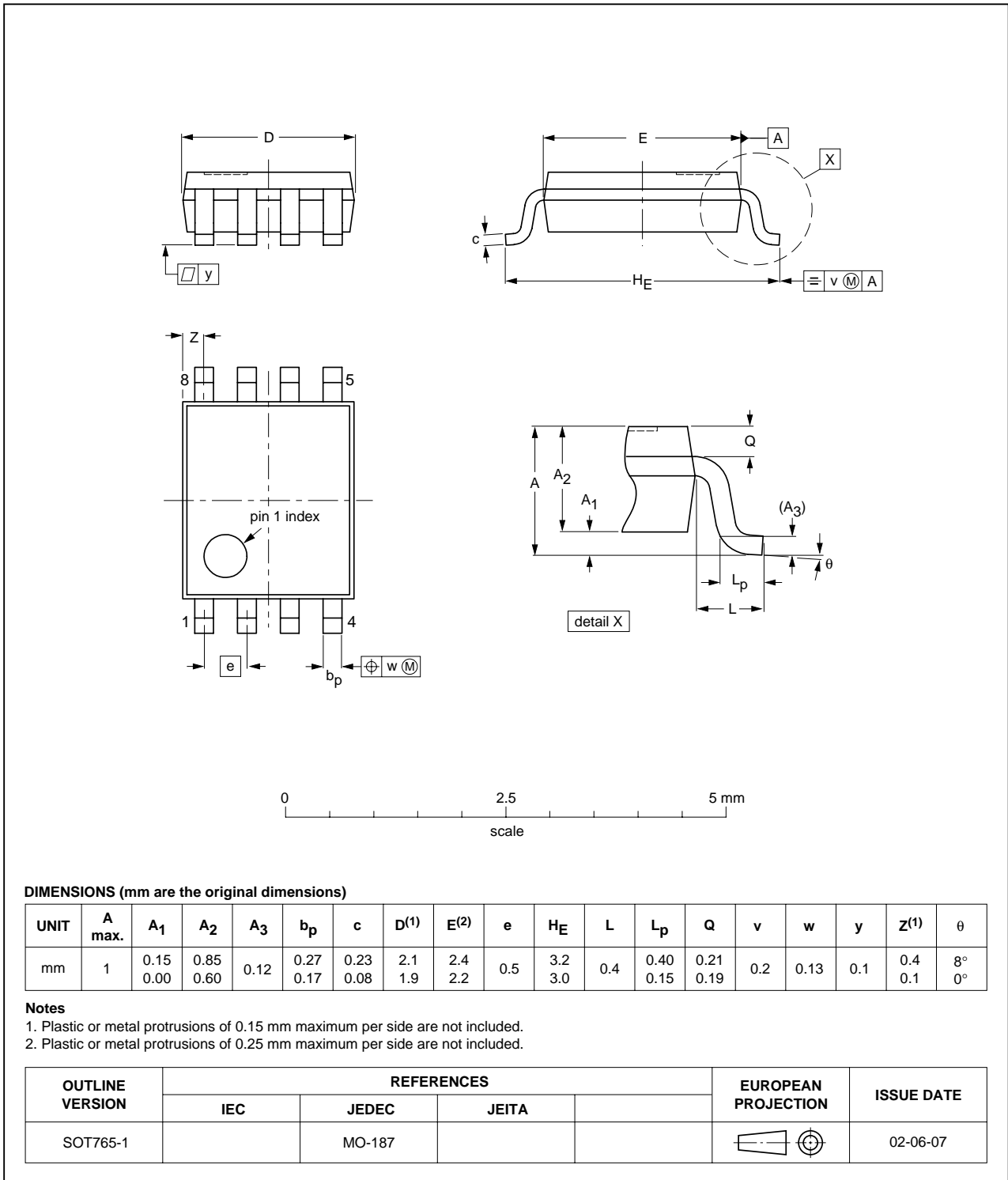


Fig 15. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

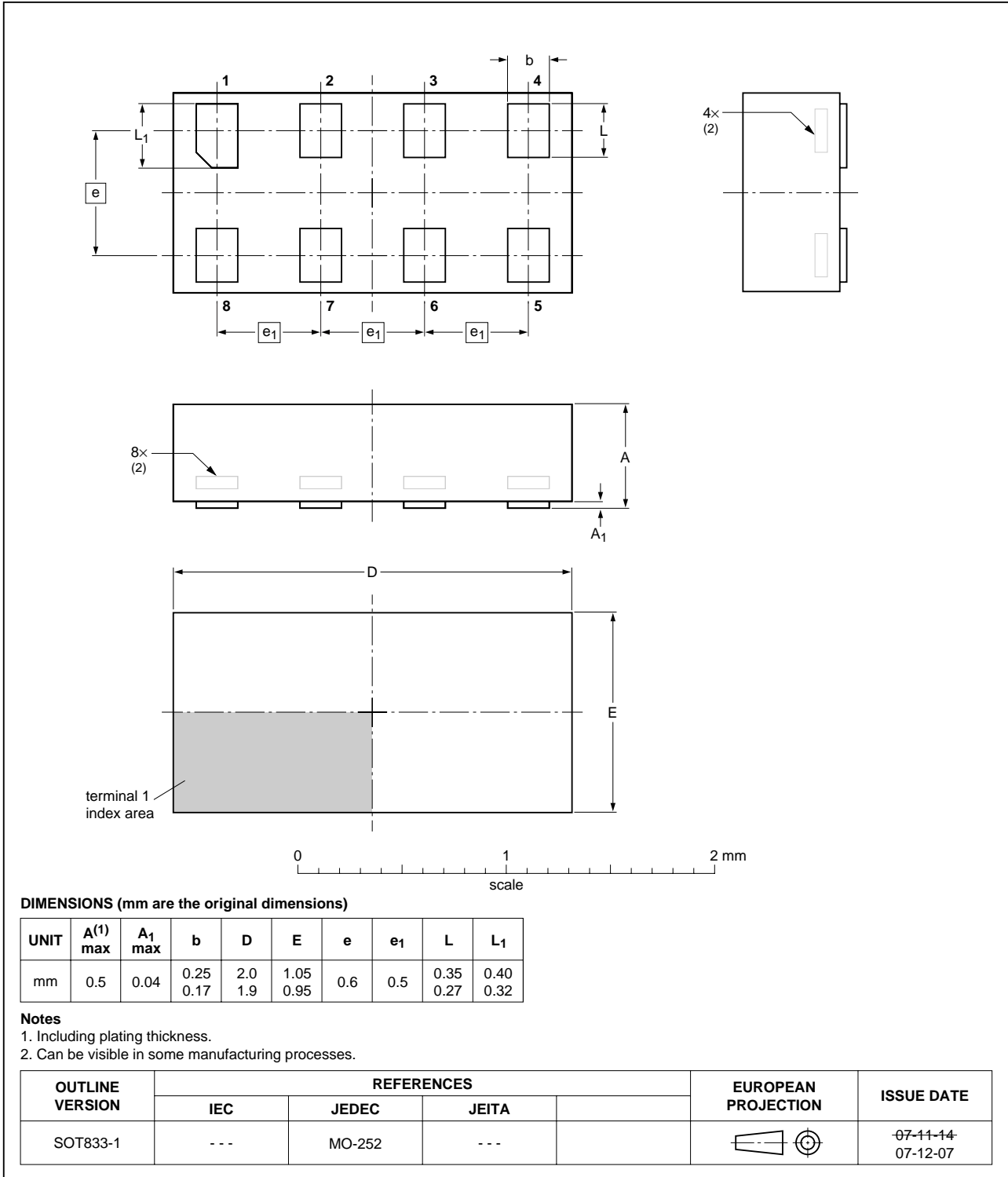


Fig 16. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

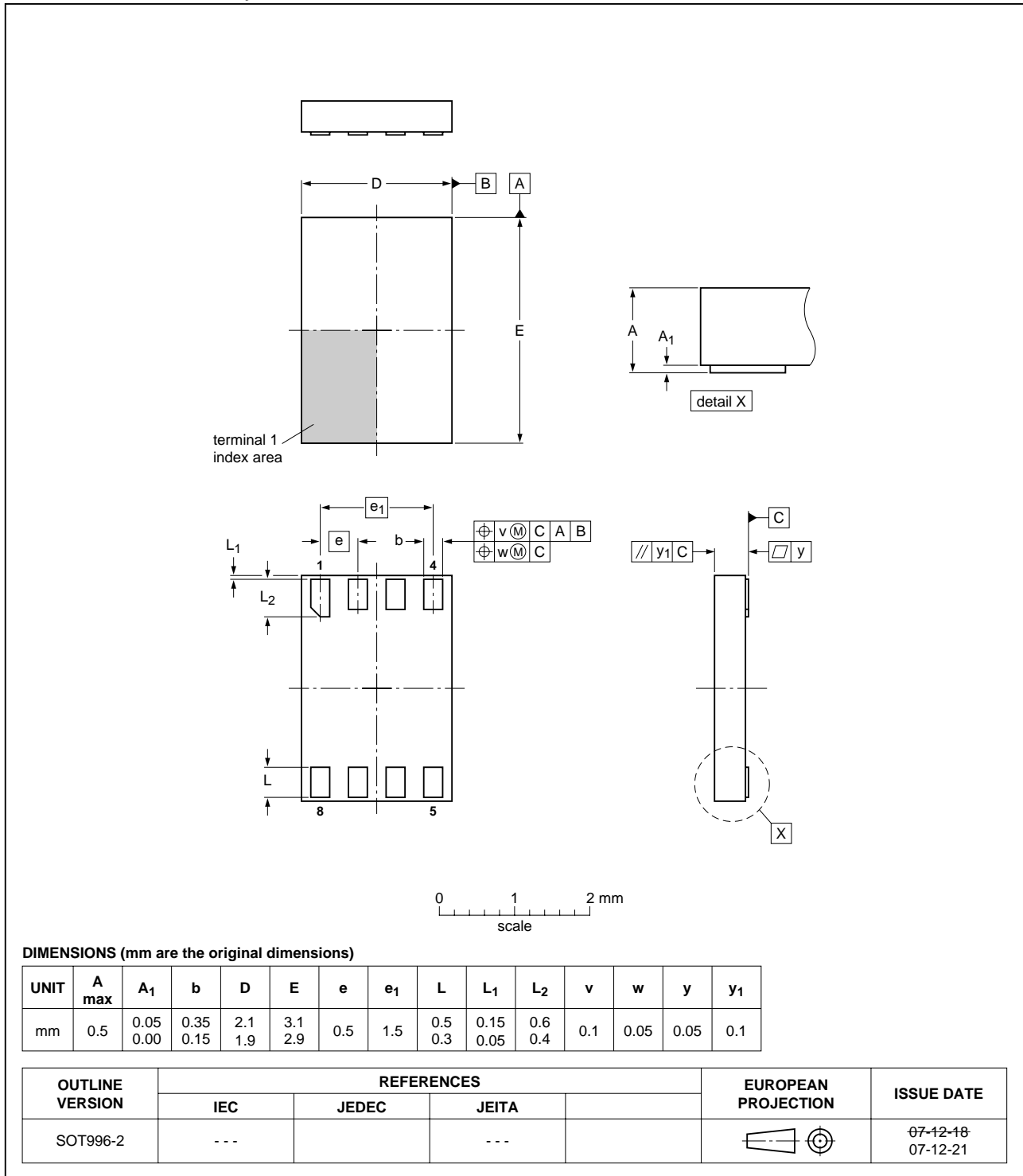


Fig 17. Package outline SOT996-2 (XSON8U)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

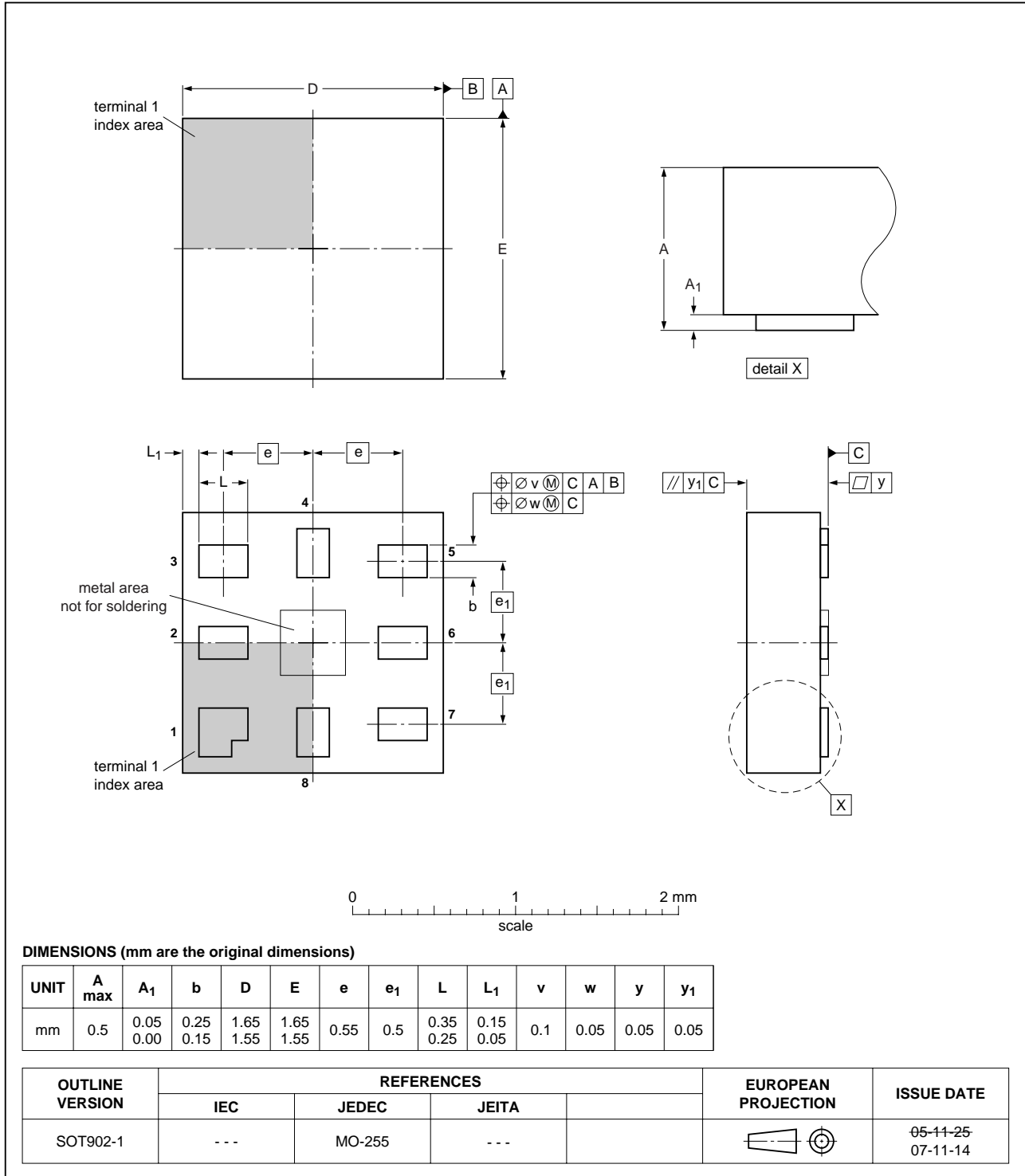


Fig 18. Package outline SOT902-1 (XQFN8U)

17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC3G17_6	20080606	Product data sheet	-	74LVC3G17_5
Modifications:	<ul style="list-style-type: none"> Added type number 74LVC3G17GD (XSON8U package) 			
74LVC3G17_5	20080313	Product data sheet	-	74LVC3G17_4
74LVC3G17_4	20070521	Product data sheet	-	74LVC3G17_3
74LVC3G17_3	20050131	Product data sheet	-	74LVC3G17_2
74LVC3G17_2	20041103	Product specification	-	74LVC3G17_1
74LVC3G17_1	20040624	Product specification	-	-

19. Legal information

19.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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